



100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
	22mΩ @ V _{GS} = 10V	47.2A
100V	30mΩ @ V _{GS} = 6.0V	40.4A
	43.7mΩ @ V _{GS} = 4.5V	33.5A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters
- Backlighting

Features

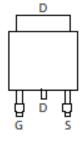
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_G Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

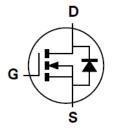
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)







Pin Out Top View



Equivalent Circuit

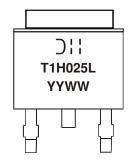
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H025LK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



Dill = Manufacturer's Marking
T1H025L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Unit			
Drain-Source Voltage		V _{DSS}	100	V		
Gate-Source Voltage		V _{GSS}	±20	V		
Continuous Drain Current, V _{GS} = 10V	T _C = +25°C	I _D	47.2	А		
Continuous Diairi Guirent, VGS = 10V	$T_C = +70$ °C		37.7			
Pulsed Drain Current (10μs Pulse, T _C = +25°C, Package Limited)		I_{DM}	185	Α		
Pulsed Body Diode Forward Current (10µs Pulse, T _C = +25°C, Package Limited)		I _{SM}	185	Α		
Maximum Continuous Body Diode Forward Current (Note 6)		aximum Continuous Body Diode Forward Current (Note 6)		Is	2.6	Α
Avalanche Current, L = 0.1mH		I _{AS}	15.8	A		
Avalanche Energy, L = 0.1mH		E _{AS}	12.5	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P _D	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	48	°C/W
Total Power Dissipation (Note 6)	P _D	83	W	
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	1.5	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

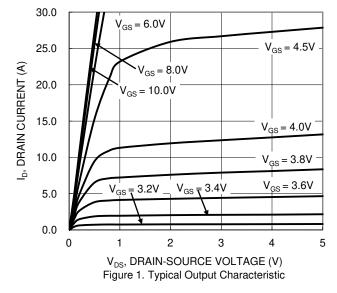
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV_{DSS}	100			V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	1	1	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	I	3	٧	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
		I	17.1	22		$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	l	21.4	30	mΩ	$V_{GS} = 6V, I_D = 20A$	
		1	28.3	43.7		$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V_{SD}	1	1	1.3	٧	$V_{GS} = 0V, I_S = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	1477	_		V _{DS} = 50V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	263	_	pF		
Reverse Transfer Capacitance	Crss	1	20	_		1 = 1101112	
Gate Resistance	R_{G}	1	1.3	1	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_{G}	1	21	_		$V_{DD} = 50V, I_D = 20A, V_{GS} = 10V$	
Gate-Source Charge	Q_{GS}	I	5.7	1	nC		
Gate-Drain Charge	Q_{GD}	1	3.8	1		VGS = 10V	
Turn-On Delay Time	t _{D(ON)}	I	6.3	1		V _{DD} = 50V, V _{GS} = 10V,	
Turn-On Rise Time	t _R	l	9.4	1	ns		
Turn-Off Delay Time	t _{D(OFF)}	I	16.7	1	115	$I_D = 20A$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _F	I	8.2	_			
Reverse Recovery Time	t _{RR}		38.7	_	ns	L 200 di/dt 1000/up	
Reverse Recovery Charge	Q _{RR}	_	53.7	_	nC	$I_F = 20A$, di/dt = 100A/ μ s	

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.





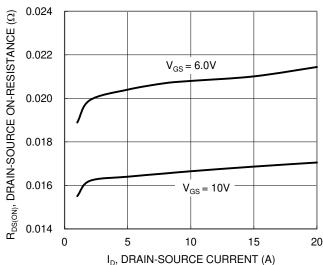


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

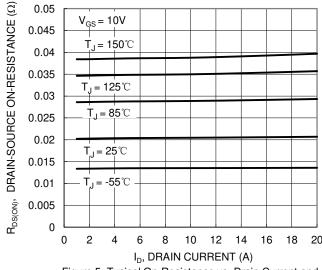
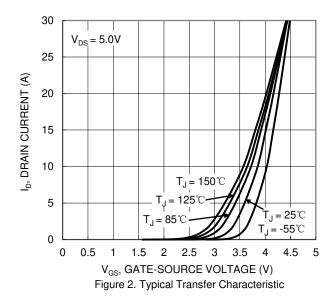
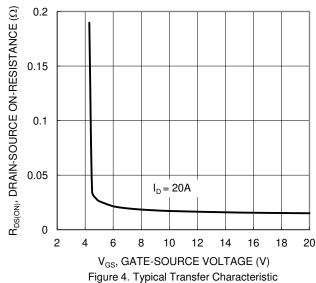


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





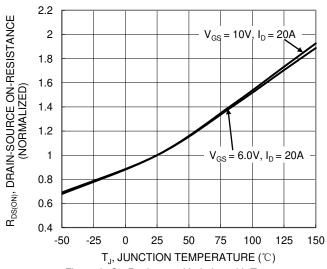


Figure 6. On-Resistance Variation with Temperature



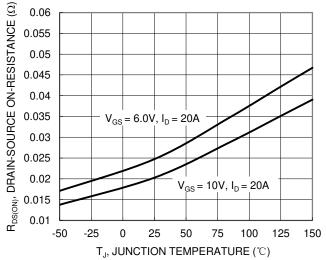


Figure 7. On-Resistance Variation with Temperature

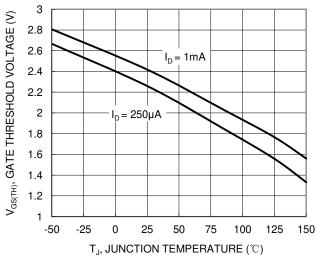


Figure 8. Gate Threshold Variation vs. Junction Temperature

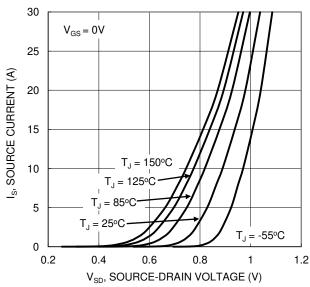
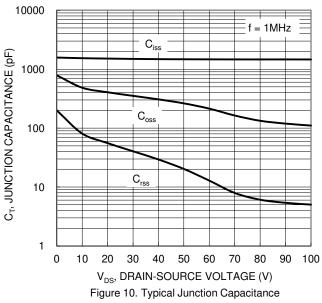
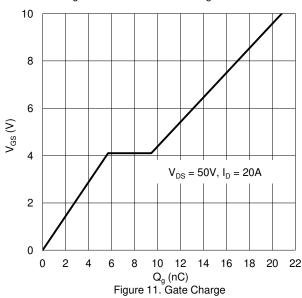


Figure 9. Diode Forward Voltage vs. Current





1000 R_{DS(ON)} Limited 100 ID, DRAIN CURRENT (A) 10 = 10µs $P_W = 100 \mu s$ $\begin{array}{l} T_{J(Max)} = 150\,^{\circ}\mathrm{C} \\ T_{C} = 25\,^{\circ}\mathrm{C} \end{array}$ Single Pulse DUT on Infinite Heatsink DC $V_{GS} = 10V$ 0.01 0.1 10 1000 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



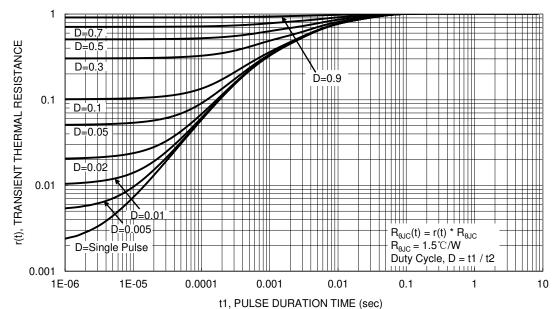


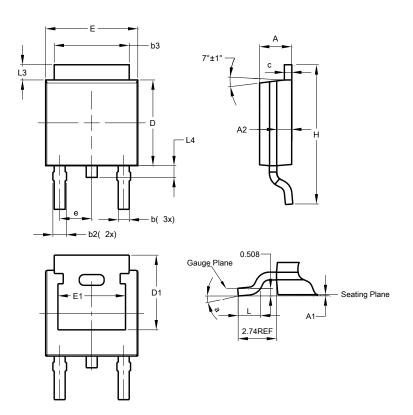
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

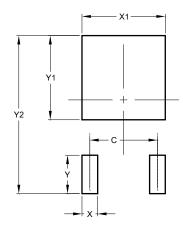


TO252 (DPAK)				
Dim	Min	Max	Тур	
Α	2.19	2.39	2.29	
A 1	0.00	0.13	0.08	
A2	0.97	1.17	1.07	
b	0.64	0.88	0.783	
b2	0.76	1.14	0.95	
b3	5.21	5.46	5.33	
С	0.45	0.58	0.531	
D	6.00	6.20	6.10	
D1	5.21	-	-	
е	-	-	2.286	
Е	6.45	6.70	6.58	
E1	4.32	-	-	
Н	9.40	10.41	9.91	
L	1.40	1.78	1.59	
L3	0.88	1.27	1.08	
L4	0.64	1.02	0.83	
а	0°	10°	-	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Υ	2.600		
Y1	5.700		
V2	10 700		



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